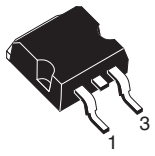
STB20NM60D

N-channel 600V - 0.26Ω - 20A - D²PAK FDmesh™ Power MOSFET

General features

Type	V_{DSS}	$R_{DS(on)}$	I_D	Pw
STB20NM60D	600V	<0.29Ω	20A	45W

- High dv/dt and avalanche capabilities
- 100% Avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance
- Tight process control and high manufacturing yields

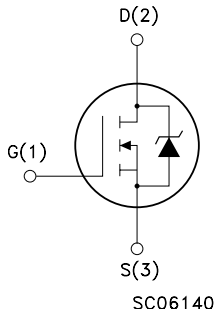


D²PAK

Description

The FDmesh™ associates all advantages of reduced on-resistance and fast switching with an intrinsic fast-recovery body diode. It is therefore strongly recommended for bridge topologies, in particular ZVS phase-shift converters.

Internal schematic diagram



Applications

- Switching application

Order codes

Part number	Marking	Package	Packaging
STB20NM60D	B20NM60D	D²PAK	Tape & reel

Contents

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage (V_{GS} = 0)	600	V
V_{DGR}	Drain-gate voltage (R_{GS} = 20 kΩ)	600	V
V_{GS}	Gate- source voltage	± 30	V
I_D	Drain current (continuous) at T_C = 25°C	20	A
I_D	Drain current (continuous) at T_C = 100°C	12.6	A
I_{DM} (1)	Drain current (pulsed)	80	A
P_{TOT}	Total dissipation at T_C = 25°C	192	W
	Derating factor	1.20	W/°C
dv/dt (2)	Peak diode recovery voltage slope	20	V/ns
T_j T_{stg}	Operating junction temperature Storage temperature	– 65 to 150	°C °C

1. Pulse width limited by safe operating area
2. $I_{SD} \leq 20A$, di/dt ≤ 400A/µs, $V_{DD} = 80\%V_{(BR)DSS}$

Table 2. Thermal resistance

Symbol	Parameter	Value	Unit
Rthj-case	Thermal resistance junction-case Max	0.65	°C/W
Rthj-amb	Thermal resistance junction-ambient Max	62.5	°C/W
T_l	Maximum lead temperature for soldering purpose	300	°C

Table 3. Avalanche data

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	10	A
E_{AS}	Single pulse avalanche energy (starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 35 V)	700	mJ

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test condictions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 250µA, V_{GS} = 0	600			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0) V_{DS} = Max rating V_{DS} = Max rating, T_C = 125 °C				1 10	µA µA
I_{GSS}	Gate-body leakage current (V_{DS} = 0)	V_{GS} = ±30V			±10 0	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS} = 10V, I_D = 10A		0.26	0.29	Ω

Table 5. Dynamic

Symbol	Parameter	Test condictions	Min	Typ	Max	Unit
g_{fs} (1)	Forward transconductance	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max}$, I_D = 10A		9		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		1300 500 35		pF pF pF
$C_{oss\ eq.}$ (2)	Equivalent output capacitance	V_{GS} = 0V, V_{DS} = 0V to 480V		190		pF
R_G	Gate input resistance	f=1 MHz Gate DC Bias = 0 Test signal level = 20mV open drain		2.7		Ω
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} = 480V, I_D = 20A, V_{GS} = 10V (see Figure 13)		37 10 17	52	nC nC nC

1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %
2. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80%

Table 6. Switching times

Symbol	Parameter	Test condictions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	V_{DD} = 300V, I_D = 10A R_G = 4.7Ω V_{GS} = 10V (see Figure 12)		25 12		ns ns
$t_{r(Voff)}$ t_f t_c	Off-voltage rise time Fall time Cross-over time	V_{DD} = 480 V, I_D = 20A, R_G = 4.7Ω, V_{GS} = 10V (see Figure 12)		8 22 30		ns ns ns

Table 7. Source drain diode

Symbol	Parameter	Test condictions	Min	Typ.	Max	Unit
I_{SD} I_{SDM} (1)	Source-drain current Source-drain current (pulsed)				20 80	A A
V_{SD} (2)	Forward on voltage	I_{SD} = 20 A, V_{GS} = 0			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 20 A, T_j = 25°C di/dt =100A/µs,V_{DD}=60V (see Figure 17)		240 1800 16		ns nC A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 20 A, T_j = 150°C di/dt =100A/µs,V_{DD}=60V (see Figure 17)		396 2960 20		ns nC A

1. Pulse width limited by safe operating area
2. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

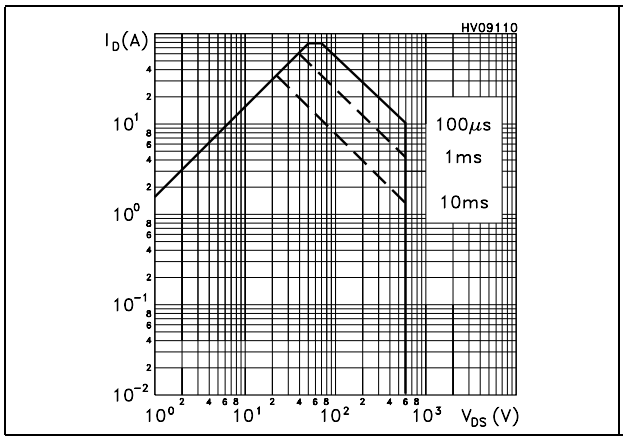


Figure 2. Thermal impedance

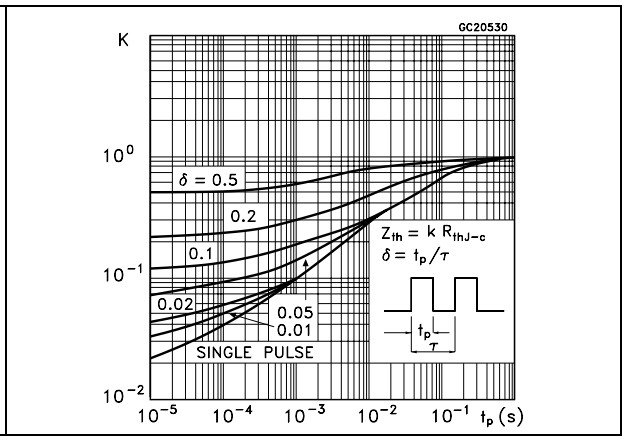


Figure 3. Output characterisics

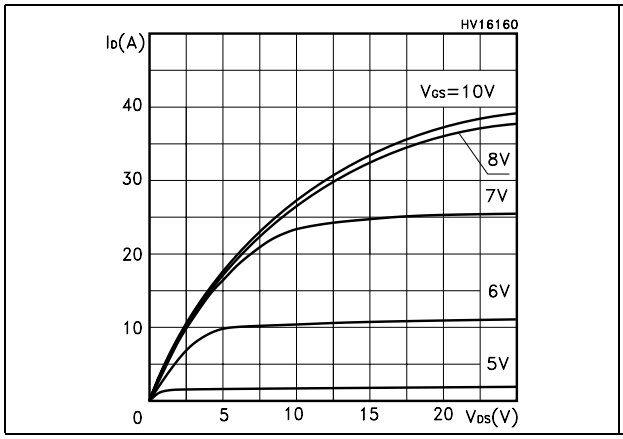


Figure 4. Transfer characteristics

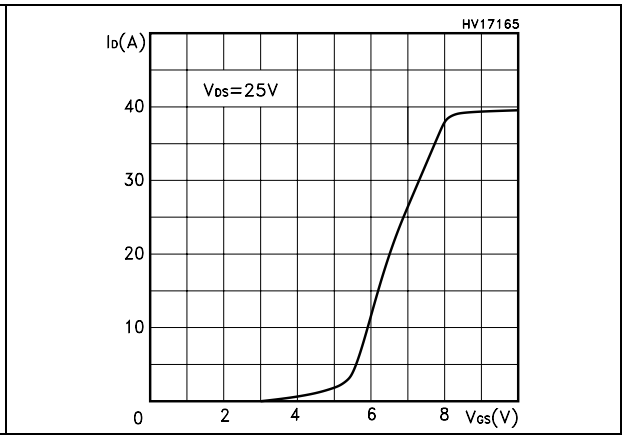


Figure 5. Transconductance

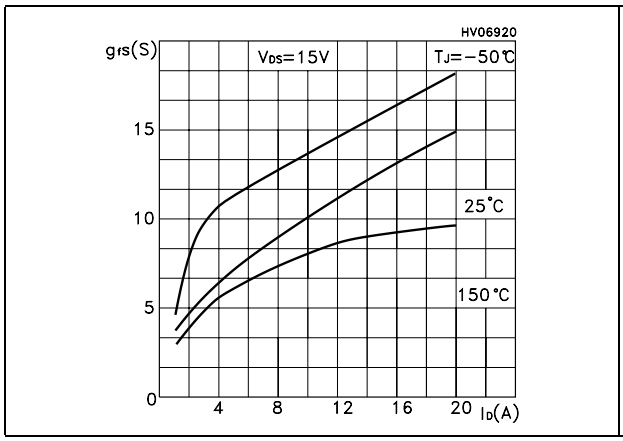


Figure 6. Static drain-source on resistance

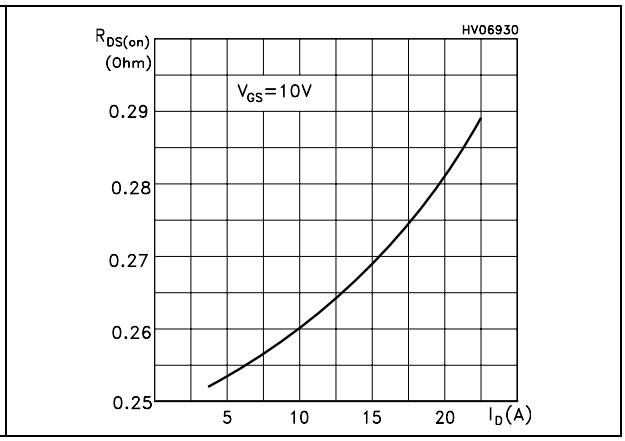


Figure 7. Gate charge vs gate-source voltage

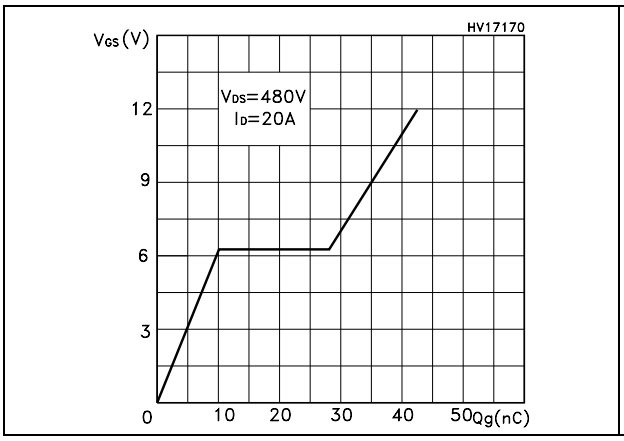


Figure 8. Capacitance variations

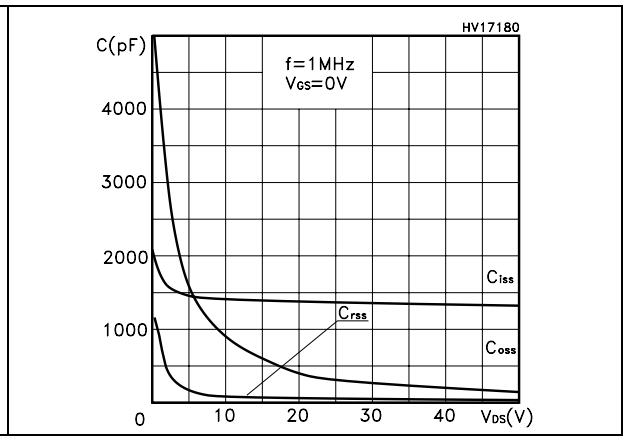


Figure 9. Normalized gate threshold voltage vs temperature

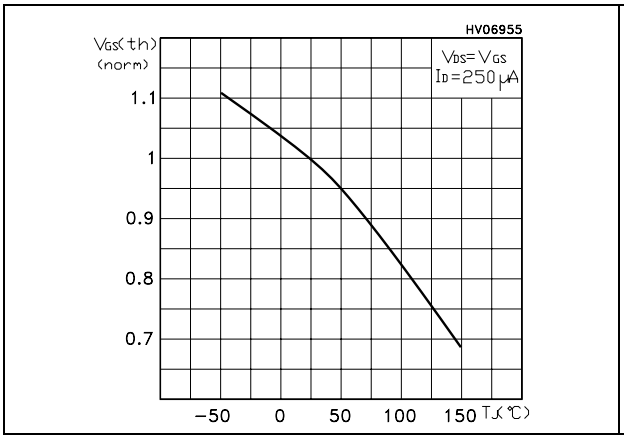


Figure 10. Normalized on resistance vs temperature

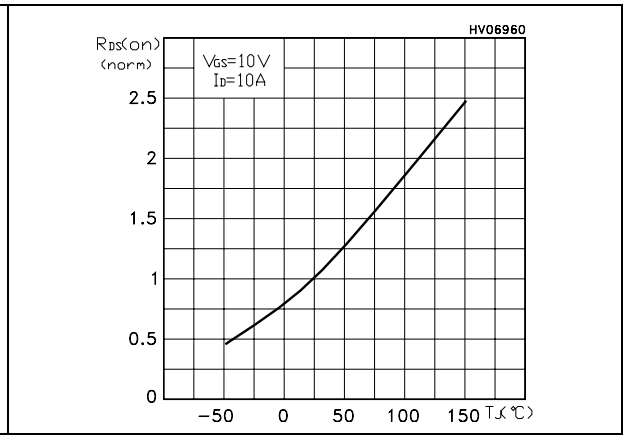
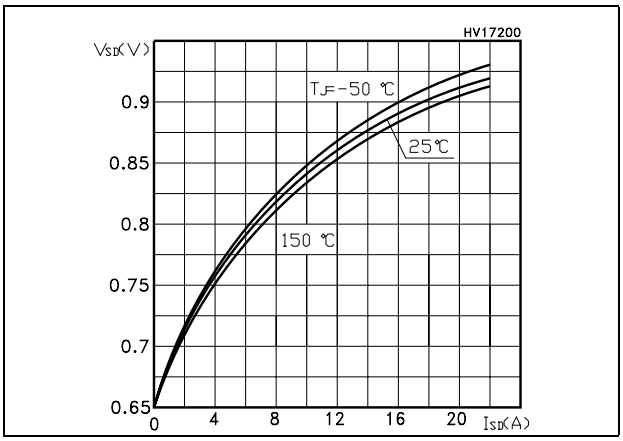


Figure 11. Source-drain diode forward characteristics



3 Test circuit

Figure 12. Switching times test circuit for resistive load

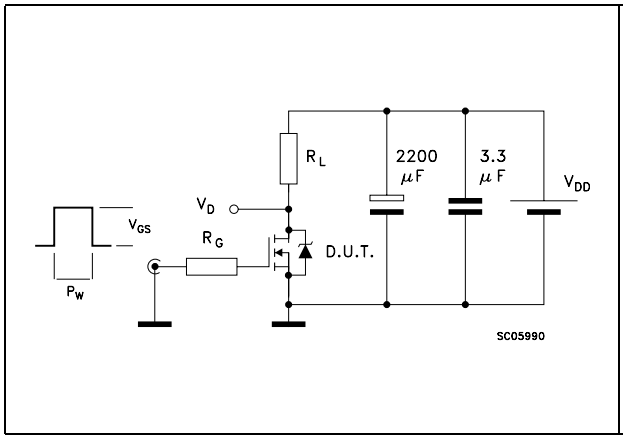


Figure 13. Gate charge test circuit

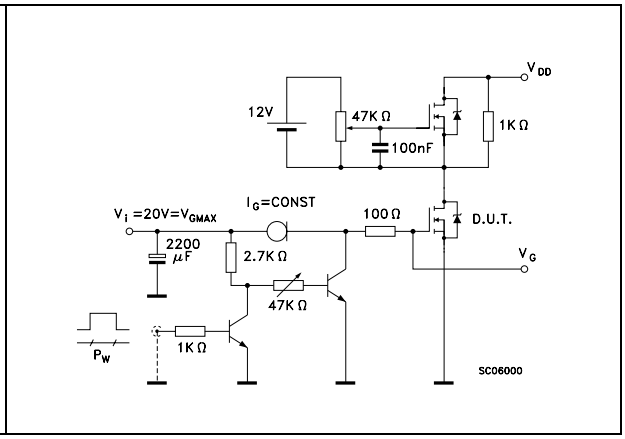


Figure 14. Test circuit for inductive load switching and diode recovery times

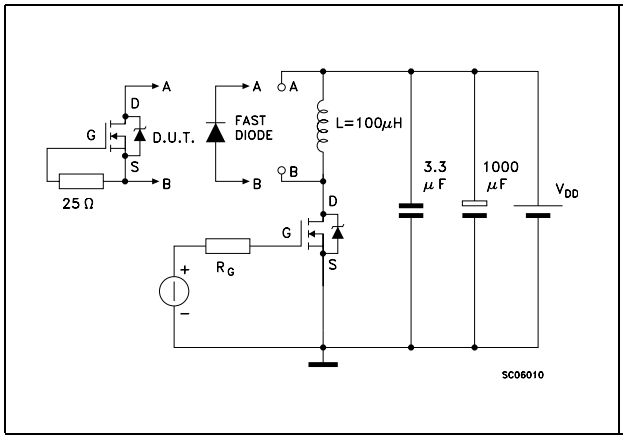


Figure 15. Unclamped inductive load test circuit

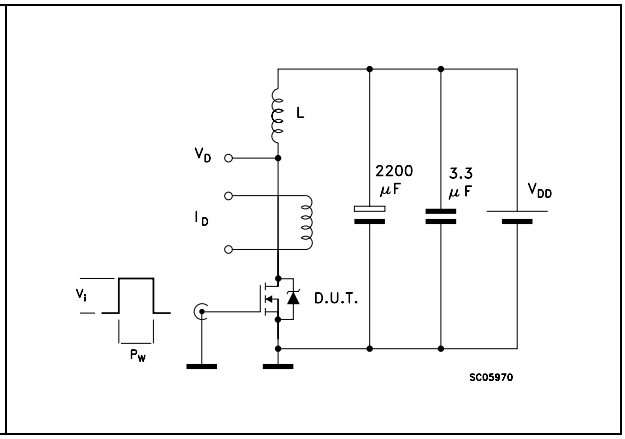


Figure 16. Unclamped inductive waveform

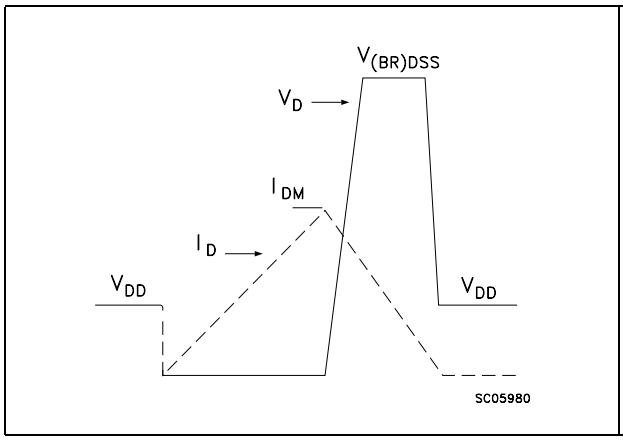
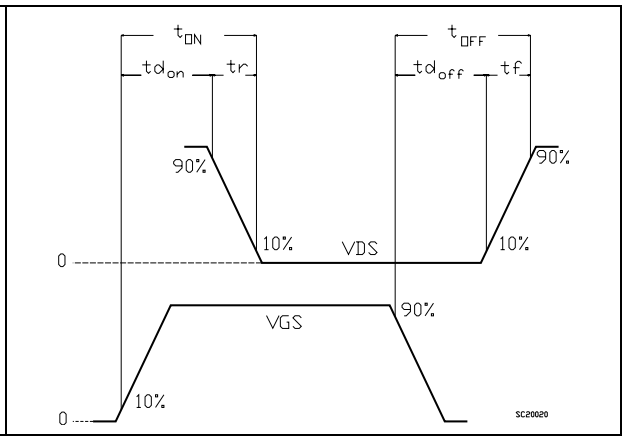


Figure 17. Switching time waveform

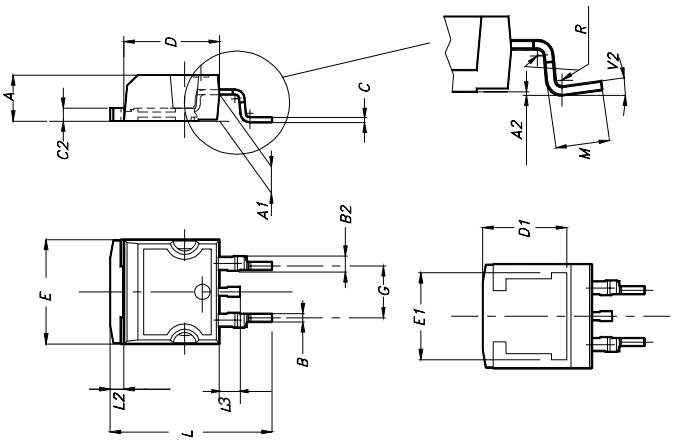


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: *www.st.com*

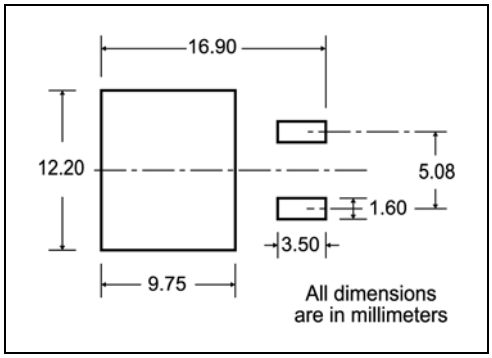
D^2PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0º		4º			

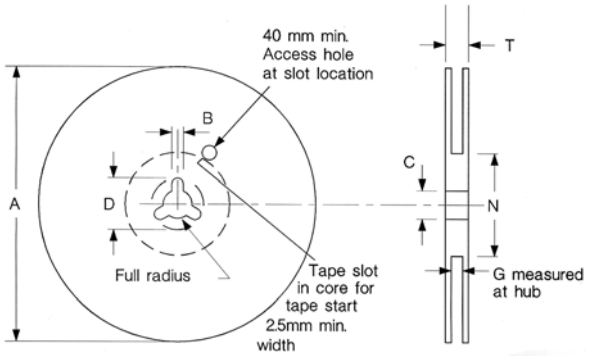


5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



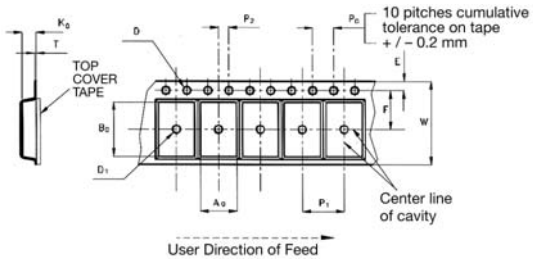
REEL MECHANICAL DATA

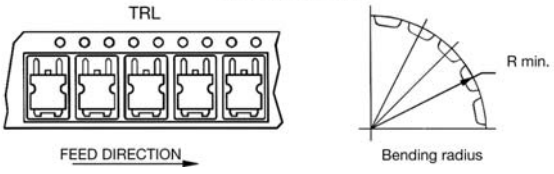
DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956





* on sales type

6 Revision history

Table 8. Revision history

Date	Revision	Changes
08-Jun-2006	1	First release

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